

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-30V	8.0m Ω @-10V	-45A
	12m Ω @-4.5V	

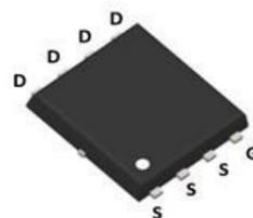
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

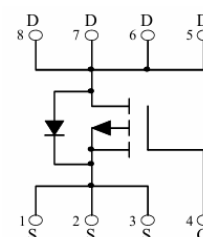
Application

- Power Management
- Load Switching
- Motor Driving
- High frequency switching, synchronous rectification

PDFN3.3X3.3-8L



Schematic diagram



Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPM090P03LNA	PDFN3.3X3.3-8L	M090P03L	Reel & Tape	330mm	12mm	5000pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	-45	A
	$T_C = 100^\circ\text{C}$		-28	
Pulsed Drain Current ²		I_{DM}	-180	A
Single Pulsed Avalanche Current ³		I_{AS}	-24	A
Single Pulsed Avalanche Energy ³		E_{AS}	144	mJ
Power Dissipation ⁵	$T_C = 25^\circ\text{C}$	P_D	31	W
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	60	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	4.0	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

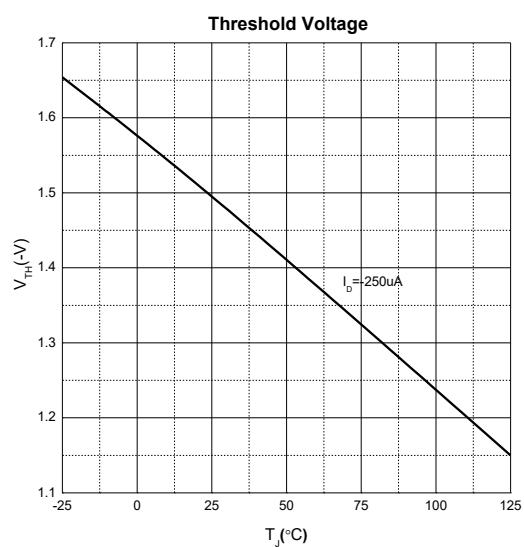
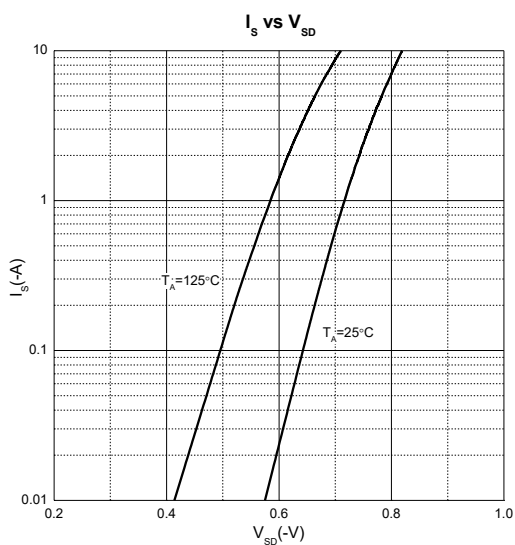
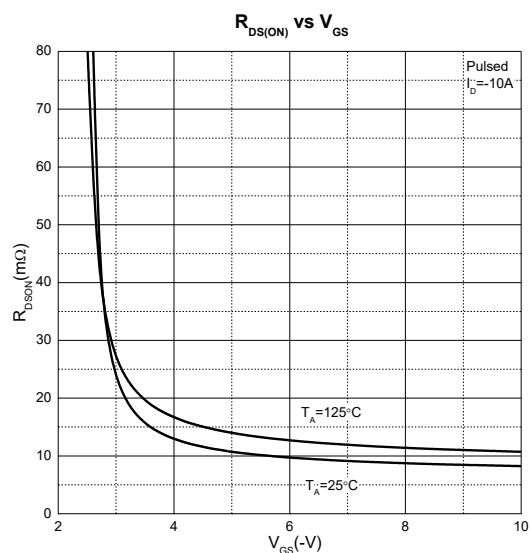
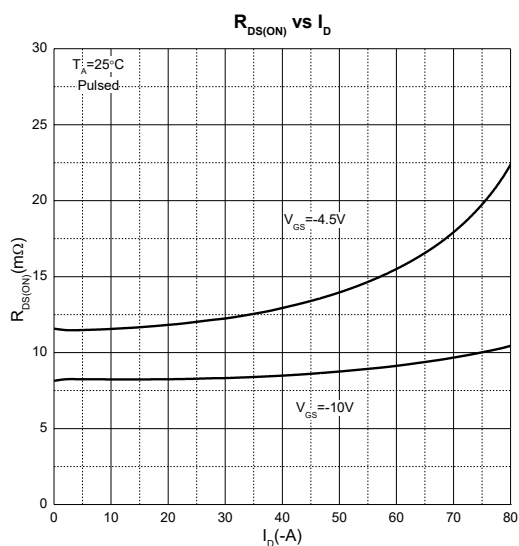
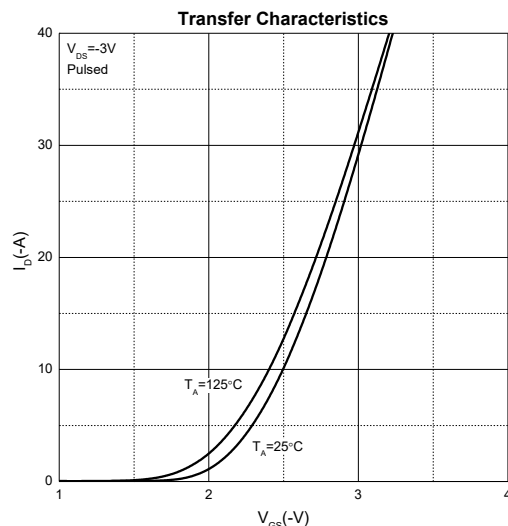
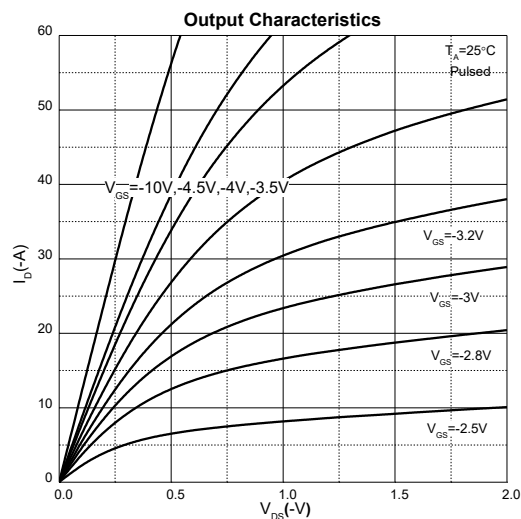
MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

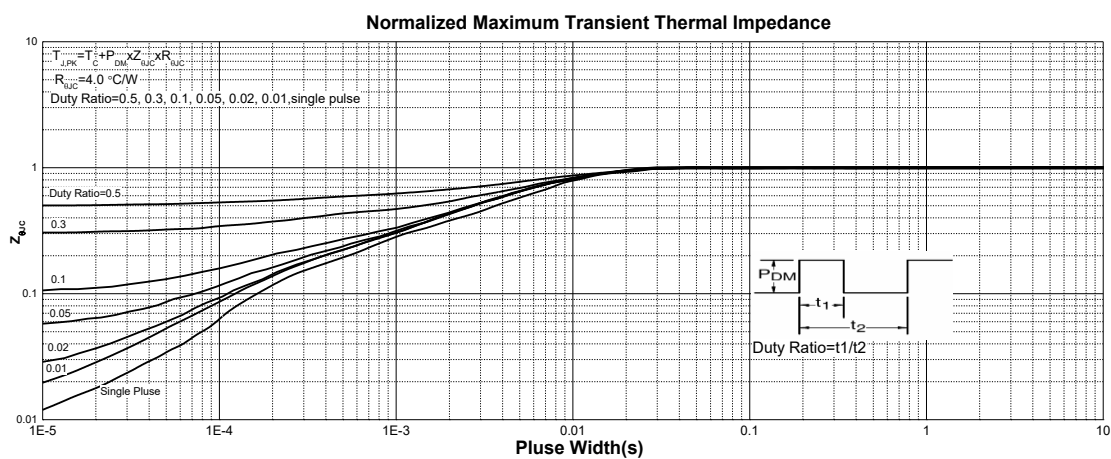
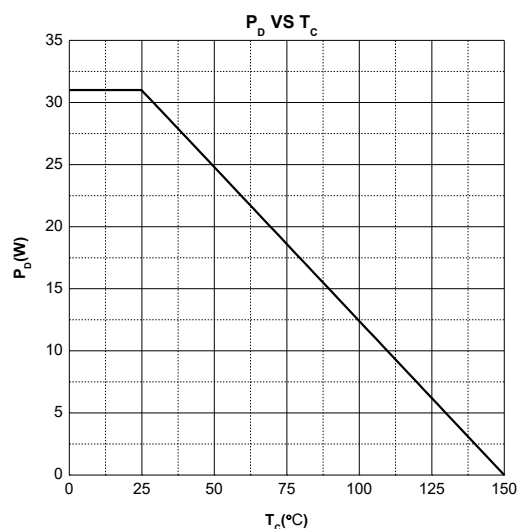
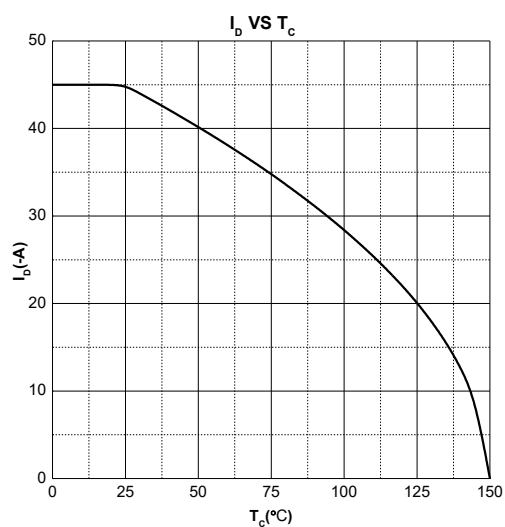
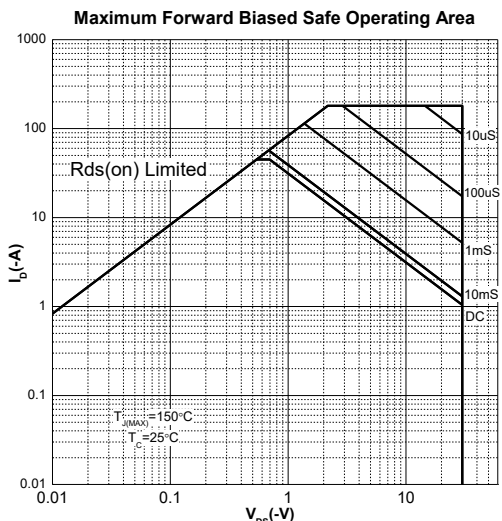
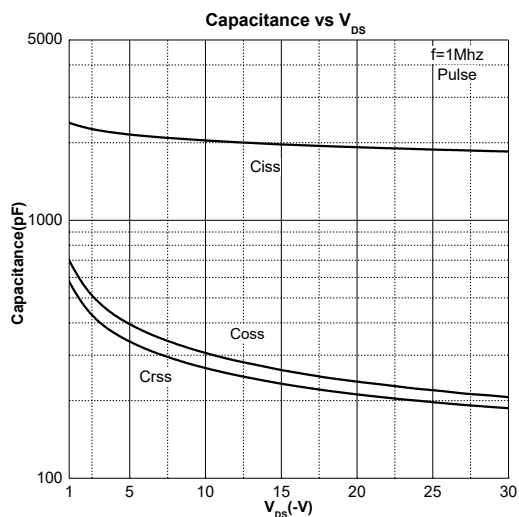
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
On Characteristics ⁴						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.0	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -10A		8.0	10.5	mΩ
		V _{GS} = -4.5V, I _D = -8A		12	18	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -5V, I _D = -20A		26		S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = -15V, V _{GS} = 0V, f = 1MHz		1992		pF
Output Capacitance	C _{oss}			264		
Reverse Transfer Capacitance	C _{rss}			233		
Gate Resistance	R _g	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz		13.7		Ω
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} = -15V, V _{GS} = -10V, I _D = -20A		42		nC
Gate-Source Charge	Q _{gs}			4.7		
Gate-Drain Charge	Q _{gd}			9.8		
Gate Plateau Voltage	V _{plateau}			2.6		V
Turn-On Delay Time	t _{d(on)}	V _{DD} = -15V, V _{GS} = -10V, I _D = -20A, R _G = 3Ω		3.5		ns
Turn-On Rise Time	t _r			15		
Turn-Off Delay Time	t _{d(off)}			85		
Turn-Off Fall Time	t _f			60		
Source-Drain Diode Characteristics						
Diode Forward Voltage ⁴	V _{SD}	V _{GS} = 0V, I _S = -20A			-1.2	V
Diode Continuous Forward Current ¹	I _S	T _C = 25°C			-45	A
Diode Pulse Forward Current ²	I _{SM}	T _C = 25°C			-180	A
Diode Reverse Recovery Time	t _{rr}	I _F = -20A, dI/dt = -100A/μs		11.8		ns
Diode Reverse Recovery Charge	Q _{rr}	I _F = -20A, dI/dt = -100A/μs		4.0		nC

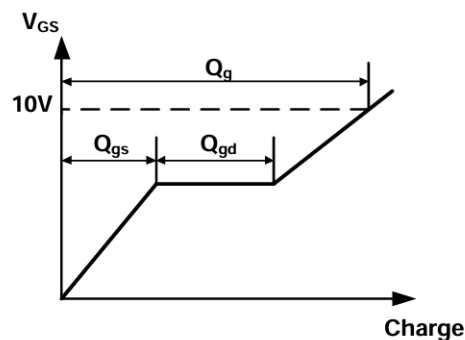
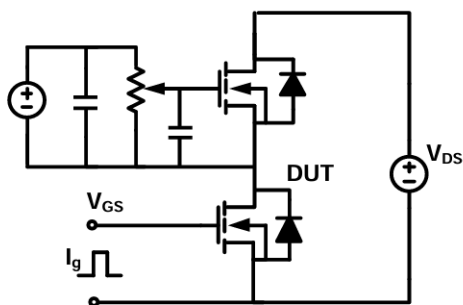
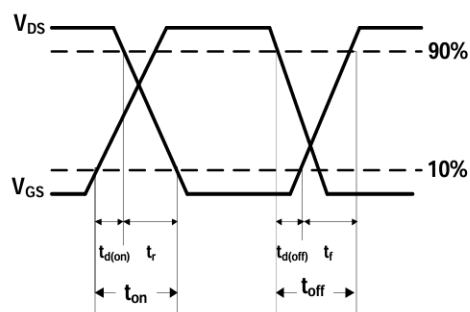
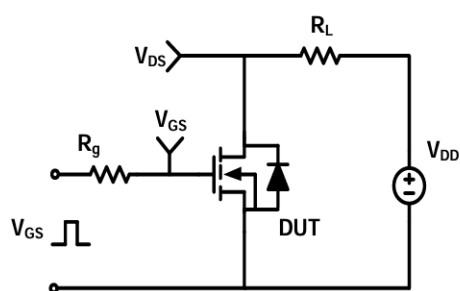
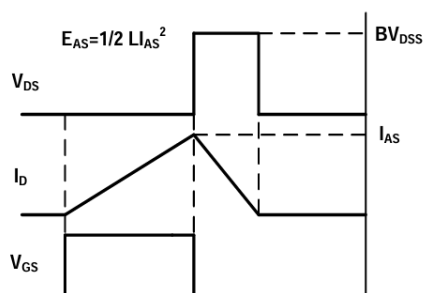
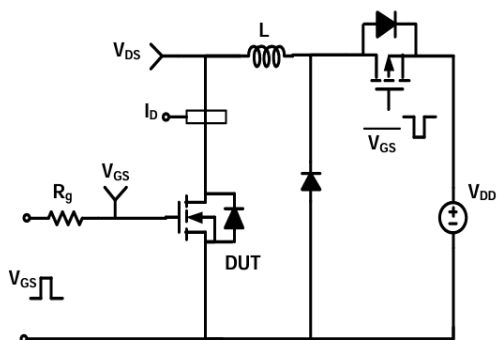
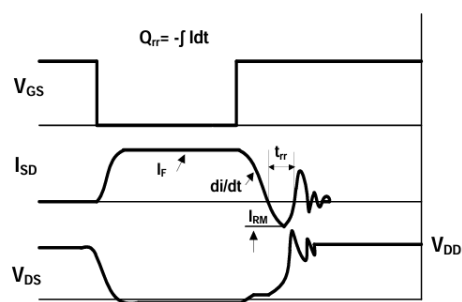
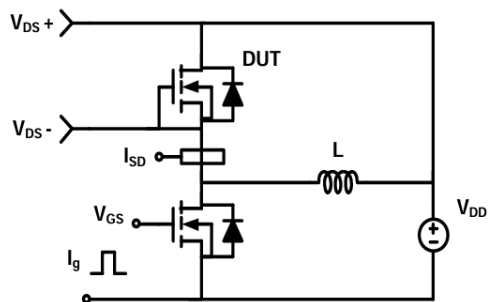
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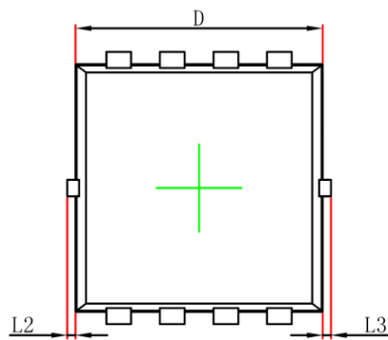
- 1.The maximum current rating is limited by package. And device mounted on a large heatsink.
- 2.Pulse Test: Pulse Width ≤ 10μs, duty cycle ≤ 1%.
- 3.EAS condition: V_{DD} = -15V, V_{GS} = -10V, L = 0.5mH, R_G = 25Ω Starting T_J = 25°C.
- 4.Pulse Test: Pulse Width ≤ 300μs, duty cycle ≤ 2%.
- 5.The power dissipation P_D is limited by T_{J(MAX)} = 150°C. And device mounted on a large heatsink.
- 6.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C.

Typical Characteristics

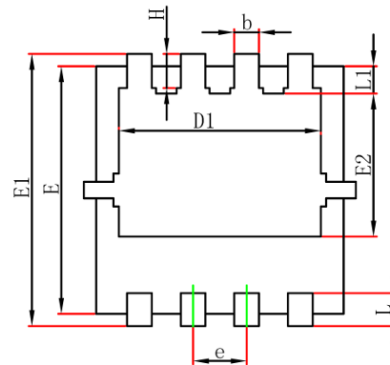




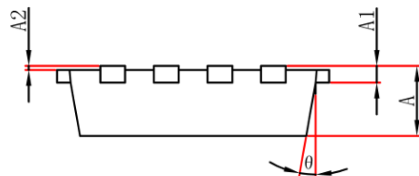
Test Circuit
Gate Charge Test Circuit & Waveform

Resistive Switching Test Circuit & Waveform

Unclamped Inductive Switching (UIS) Test Circuit & Waveform

Diode Recovery Test Circuit & Waveform


PDFN3.3X3.3-8L Package Information


Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.152REF		0.006REF	
A2	0.000	0.050	0.000	0.002
D	2.900	3.200	0.114	0.126
D1	2.300	2.600	0.091	0.102
E	2.900	3.200	0.114	0.126
E1	3.150	3.450	0.124	0.136
E2	1.535	1.935	0.060	0.076
b	0.200	0.400	0.008	0.016
e	0.550	0.750	0.022	0.030
L	0.300	0.500	0.012	0.020
L1	0.180	0.480	0.007	0.019
L2	0.000	0.100	0.000	0.004
L3	0.000	0.100	0.000	0.004
H	0.315	0.515	0.012	0.020
θ	0°	12°	0°	12°

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.